Features

- Interdigitated amplifying gates
- Fast turn-on and high di/dt
- Low switching losses
- Short turn-off time
- Hermetic metal cases with ceramic insulators

Typical Applications

- Inductive heating
- Electronic welders
- Self-commutated inverters
- AC motor speed control

$I_{T(AV)}$	**2600A**
V_{DRM}/V_{RRM}	**1200 ～ 1400V**
t_q	**10 ～ 25μs**
I_{TSM}	**35.0 kA**

SYMBOL	CHARACTERISTIC	TEST CONDITIONS		T_j(°C)	VALUE			UNIT
					Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Double side cooled	T_C=55°C	125			2600	A
			T_C=70°C	125			2200	A
I_{DRM} I_{RRM}	Repetitive peak current	at V_{DRM} tp=10ms at V_{RRM} tp=10ms		125			300	mA
I_{TSM}	Surge on-state current	10ms half sine wave V_R=0.6V_{RRM}		125			35	kA
I^2t	I^2t for fusing coordination						6125	10^3A^2s
V_{TO}	Threshold voltage			125			1.38	V
r_T	On-state slope resistance						0.20	mΩ
V_{TM}	Peak on-state voltage	I_{TM}=4000A, F=40kN		25			2.50	V
dv/dt	Critical rate of rise of off-state voltage	V_{DM}=67%V_{DR}		125			1000	V/μs
di/dt	Critical rate of rise of on-state current	V_{DM}=67%V_{DRM}, Gate pulse t_r≤0.5μs I_{GM}=1.5A		125			1500	A/μs
Q_{rr}	Recovery charge	I_{TM}=2000A, tp=4000μs, di/dt=-20A/μs,V_R=50V		125		60		μC
tq	Circuit commutated turn-off time	I_{TM}=2000A,tp=4000μs, V_R=50V dv/dt=30V/μs ,di/dt=-20A/μs		125	10		25	μs
I_{GT}	Gate trigger current	V_A=12V, I_A=1A		25	40		300	mA
V_{GT}	Gate trigger voltage				0.8		3.0	V
I_H	Holding current				20		1000	mA
V_{GD}	Non-trigger gate voltage	V_{DM}=67%V_{DRM}		125			0.3	V
$R_{th(j-c)}$	Thermal resistance Junction to case	D.C. Double side cooled Clamping force 40kN					0.010	°C /W
$R_{th(c-h)}$	Thermal resistance case to heatsink						0.003	
F_m	Mounting force				35		47	kN
T_{vj}	Junction temperature				-40		125	°C
T_{stg}	Stored temperature				-40		140	°C
W_t	Weight					1100		g
Outline	P17							

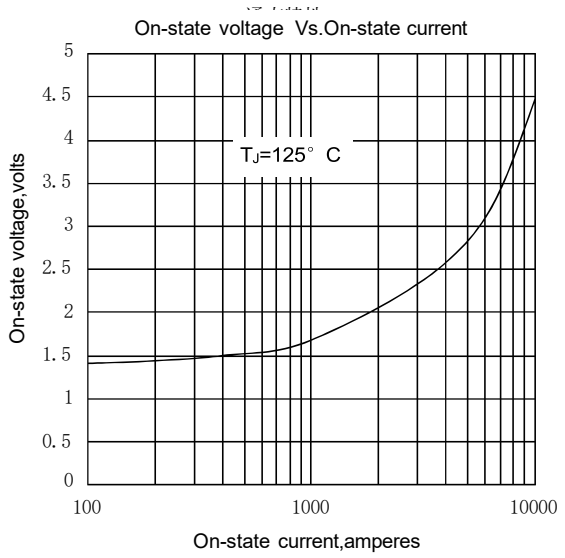


Fig.1

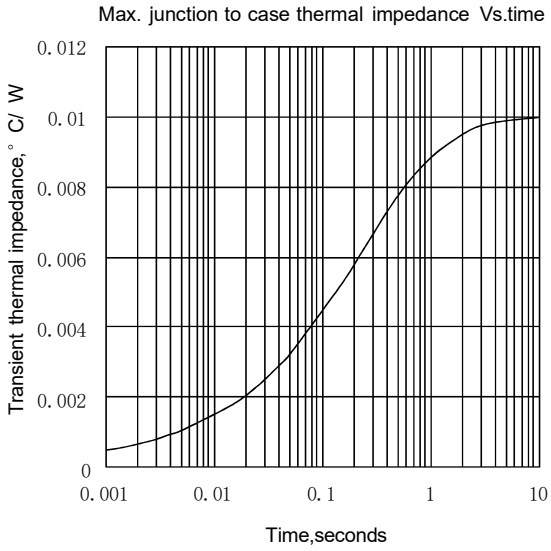


Fig.2

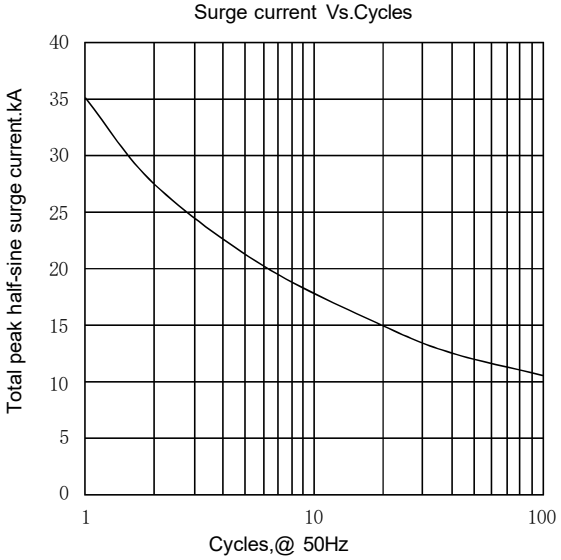


Fig.3

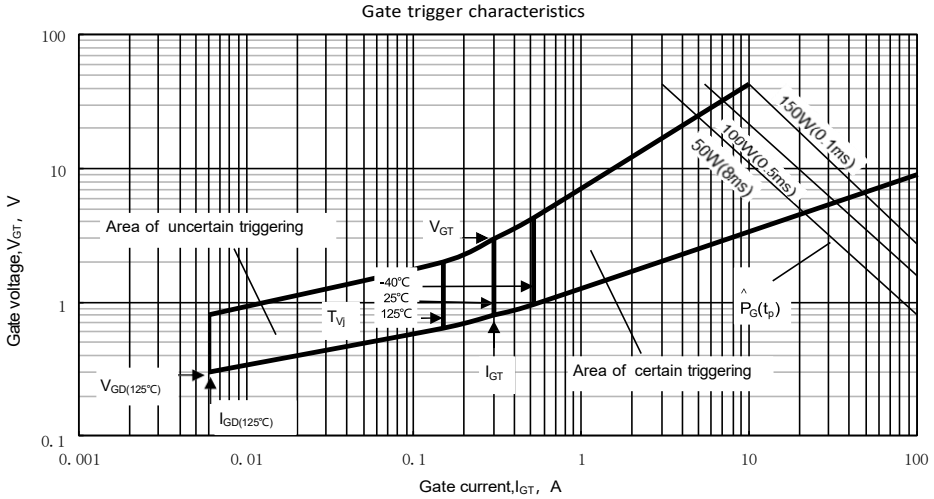
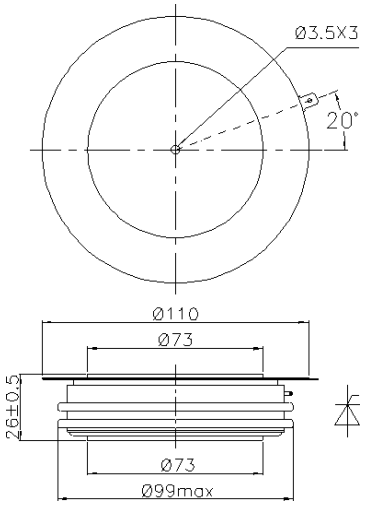


Fig.4

Outline:



NIps reserves the right to change specifications without notice.